ECE 546
Lecture - 09
Nonideal Conductors and Dielectrics

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Material Medium

$$\nabla \times \vec{E} = -\frac{\partial \mu \vec{H}}{\partial t}$$ **or** $$\nabla \times \vec{E} = -j\omega\mu\vec{H}$$

$$\nabla \times \vec{H} = \vec{J} + \frac{\partial \varepsilon \vec{E}}{\partial t}$$ $$\nabla \times \vec{H} = \vec{J} + j\omega\varepsilon\vec{E}$$

$$\vec{J} = \sigma\vec{E}$$

σ: conductivity of material medium (Ω⁻¹m⁻¹)

$$\nabla \times \vec{H} = \sigma\vec{E} + j\omega\varepsilon\vec{E} = \vec{E}\left(\sigma + j\omega\varepsilon\right) = j\omega\varepsilon\left(1 + \frac{\sigma}{j\omega\varepsilon}\right)\vec{E}$$

since $\varepsilon \rightarrow \varepsilon\left(1 + \frac{\sigma}{j\omega\varepsilon}\right)$ **then** $\nabla^2\vec{E} = -\omega^2\mu\varepsilon\left(1 + \frac{\sigma}{j\omega\varepsilon}\right)\vec{E}$

Wave in Material Medium

$$\nabla^2 \vec{E} = -\omega^2 \mu\varepsilon \left(1 + \frac{\sigma}{j\omega\varepsilon} \right) \vec{E} = \gamma^2 \vec{E}$$

$$\gamma^2 = -\omega^2 \mu\varepsilon \left(1 + \frac{\sigma}{j\omega\varepsilon} \right)$$

γ is complex propagation constant

$$\gamma = j\omega\sqrt{\mu\varepsilon}\sqrt{1 + \frac{\sigma}{j\omega\varepsilon}} = \alpha + j\beta$$

α: associated with attenuation of wave

β: associated with propagation of wave

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Wave in Material Medium

Solution: $\vec{E} = \hat{x}E_o e^{-\gamma z} = \hat{x}E_o e^{-\alpha z} e^{-j\beta z}$ decaying exponential

$$\alpha = \omega\sqrt{\frac{\mu\varepsilon}{2}}\left[\sqrt{1+\left(\frac{\sigma}{\omega\varepsilon}\right)^2}-1\right]^{1/2}$$

$$\beta = \omega\sqrt{\frac{\mu\varepsilon}{2}}\left[\sqrt{1+\left(\frac{\sigma}{\omega\varepsilon}\right)^2}+1\right]^{1/2}$$

Complex intrinsic impedance

Magnetic field

$$\vec{H} = \hat{y}\frac{E_o}{\eta}e^{-\alpha z}e^{-j\beta z}$$

$$\eta = \sqrt{\frac{j\omega\mu}{\sigma+j\omega\varepsilon}}$$

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Wave in Material Medium

$\dfrac{\sigma}{\omega\varepsilon}$ is the loss tangent

Two special cases can be distinguished:

$\dfrac{\sigma}{\omega\varepsilon} \ll 1$: poor conductor

$$\alpha \simeq \frac{\sigma}{2}\sqrt{\frac{\mu}{\varepsilon}}\left(1 - \frac{\sigma^2}{8\omega^2\varepsilon^2}\right) \simeq \frac{\sigma}{2}\sqrt{\frac{\mu}{\varepsilon}}$$

$$\beta \simeq \omega\sqrt{\mu\varepsilon}\left(1 + \frac{\sigma^2}{8\omega^2\varepsilon^2}\right) \simeq \omega\sqrt{\mu\varepsilon}$$

$$\eta \simeq \sqrt{\frac{\mu}{\varepsilon}}\left[1 - \frac{3\sigma^2}{8\omega^2\varepsilon^2} + j\frac{\sigma}{2\omega\varepsilon}\right]$$

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Wave in Material Medium

$$\frac{\sigma}{\omega\varepsilon} \gg 1 : \text{good conductor}$$

$$\gamma = \sqrt{j\omega\mu(\sigma + j\omega\varepsilon)} \simeq \sqrt{j\omega\mu\sigma} = \sqrt{\omega\mu\sigma}\,e^{j\pi/4}$$

$$\gamma \simeq \sqrt{\pi f \mu\sigma}\,(1+j)$$

$$\alpha = \sqrt{\pi f \mu\sigma} \qquad\qquad \beta = \sqrt{\pi f \mu\sigma}$$

$$\eta = \sqrt{\frac{\pi f \mu}{\sigma}}\,(1+j)$$

Skin Depth

$$\vec{E} = \hat{x}E_o e^{-\gamma z} = \hat{x}E_o e^{-\alpha z}e^{-j\beta z}$$ ← **Wave decay**

The decay of electromagnetic wave propagating into a conductor is measured in terms of the *skin depth*

Definition: skin depth δ is distance over which amplitude of wave drops by *1/e*.

$$\delta = \frac{1}{\alpha}$$

For good conductors: $\delta = \sqrt{\dfrac{2}{\omega\mu\sigma}}$

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Skin Depth

WAVE MOTION IN CONDUCTIVE MEDIA

e^{-1}

δ

Wave motion
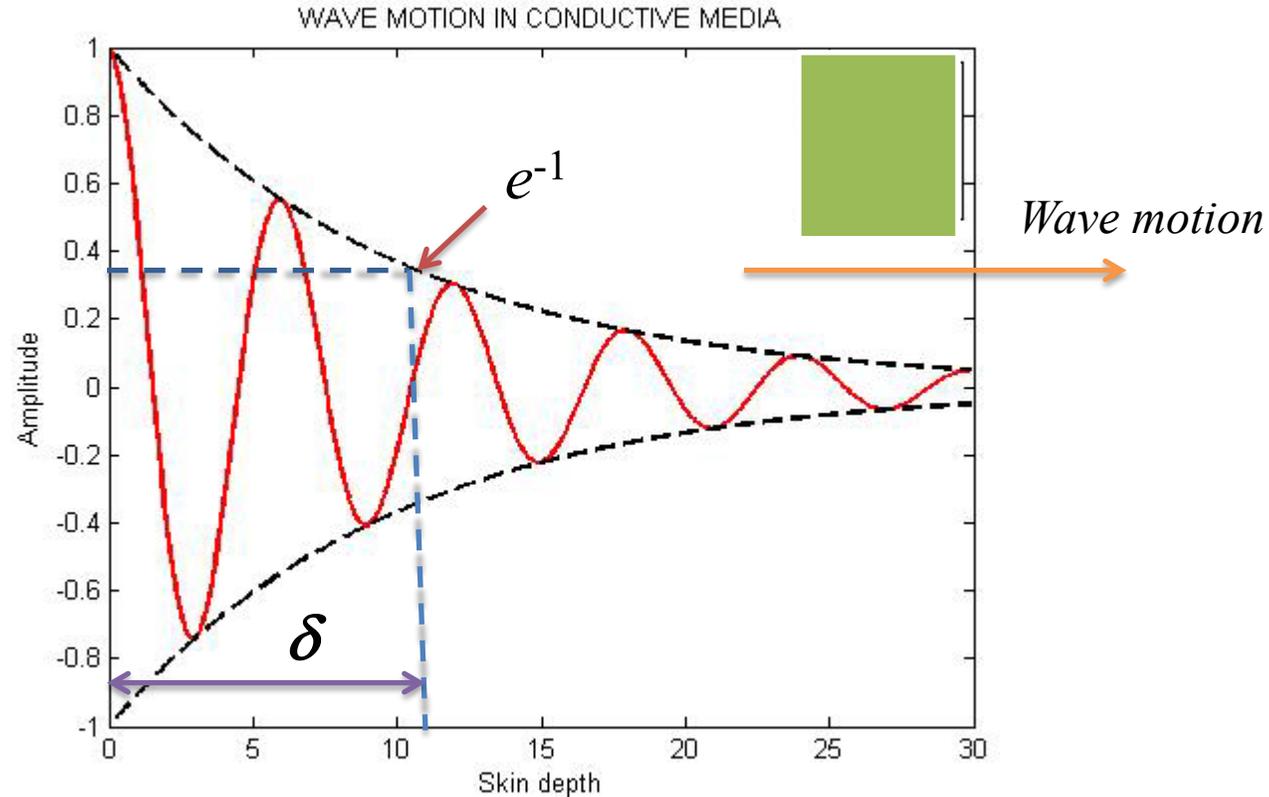
For perfect conductor, $\delta = 0$ and current only flows on the surface

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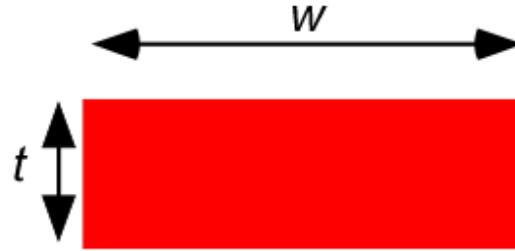
DC Resistance

$$R_{dc} = \frac{l}{\sigma w t}$$

l: conductor length
σ: conductivity

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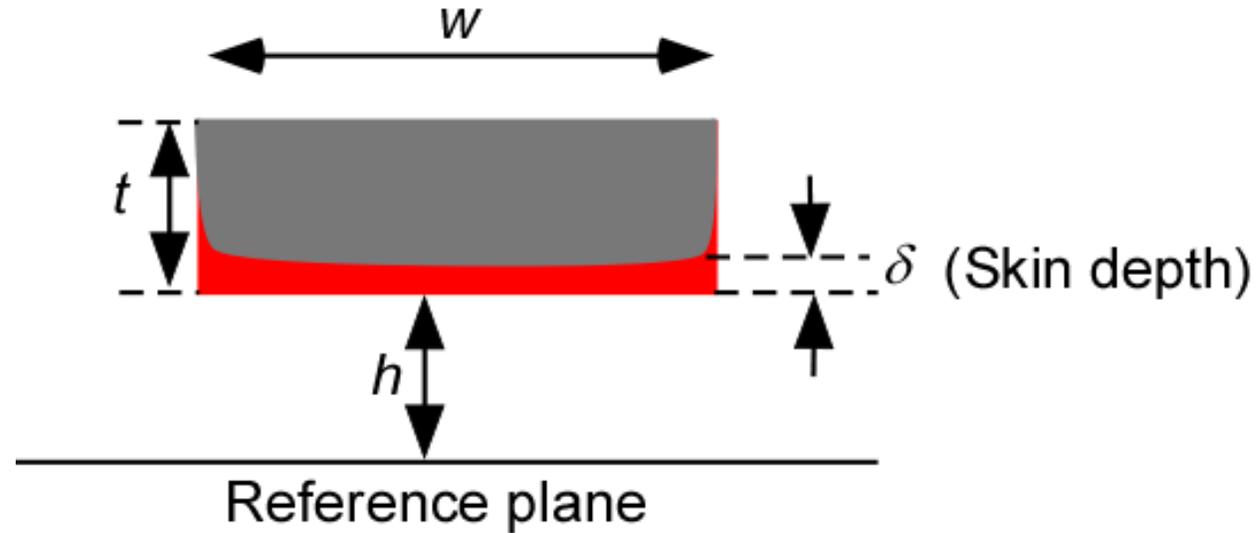
AC Resistance

$$R_{ac} = \frac{l}{\sigma w \delta} = \frac{l}{\sigma w \sqrt{2/\omega\mu\sigma}} = \frac{l}{w}\sqrt{\frac{\pi\mu f}{\sigma}}$$

l: conductor length
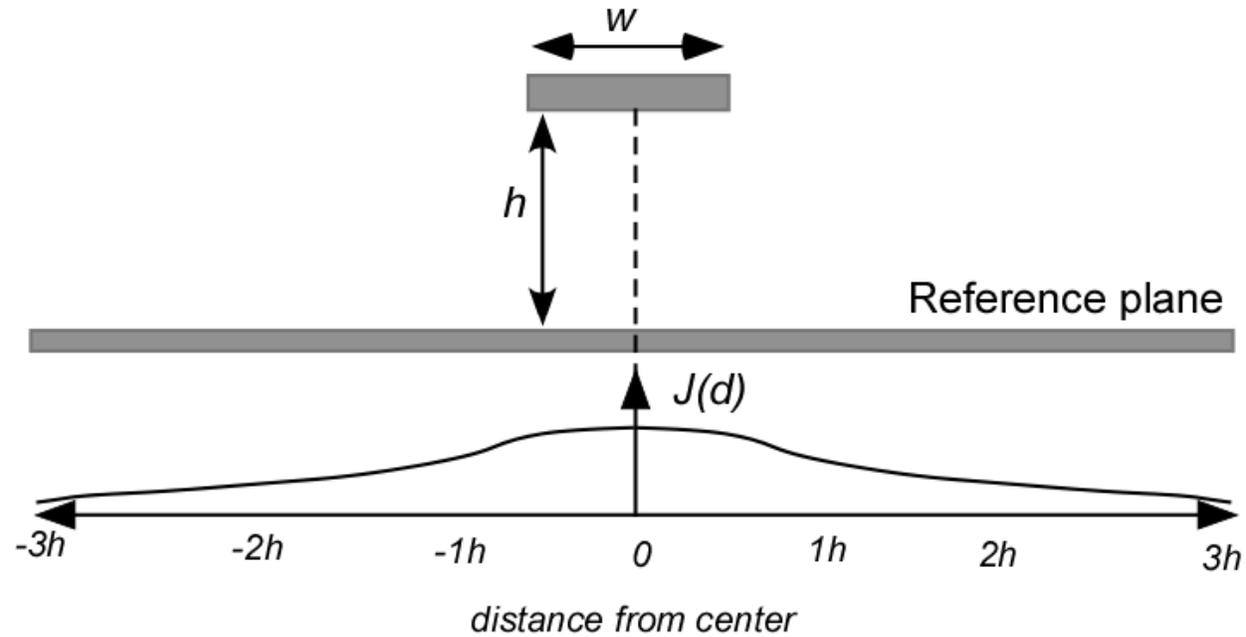σ: conductivity
f: frequency

Frequency-Dependent Resistance

$$J\delta = 1$$

$$J\int_{0}^{\infty} e^{-\alpha z}\,dz = \frac{J}{\alpha} = J\delta$$
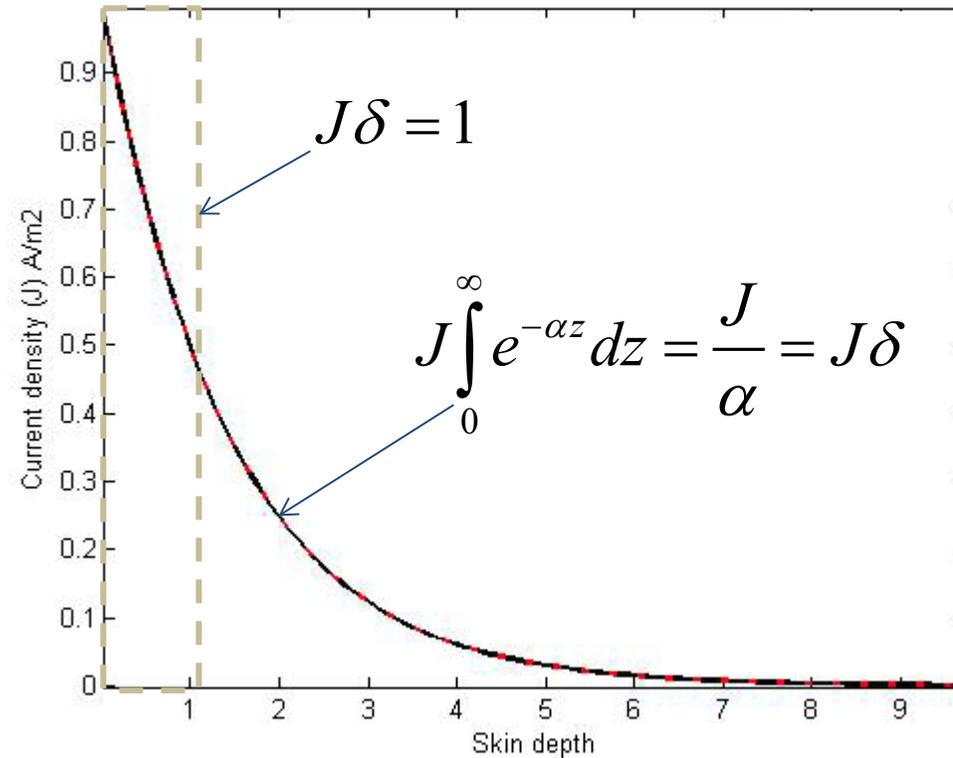
Approximation is to assume that all the current is flowing uniformly within a skin depth
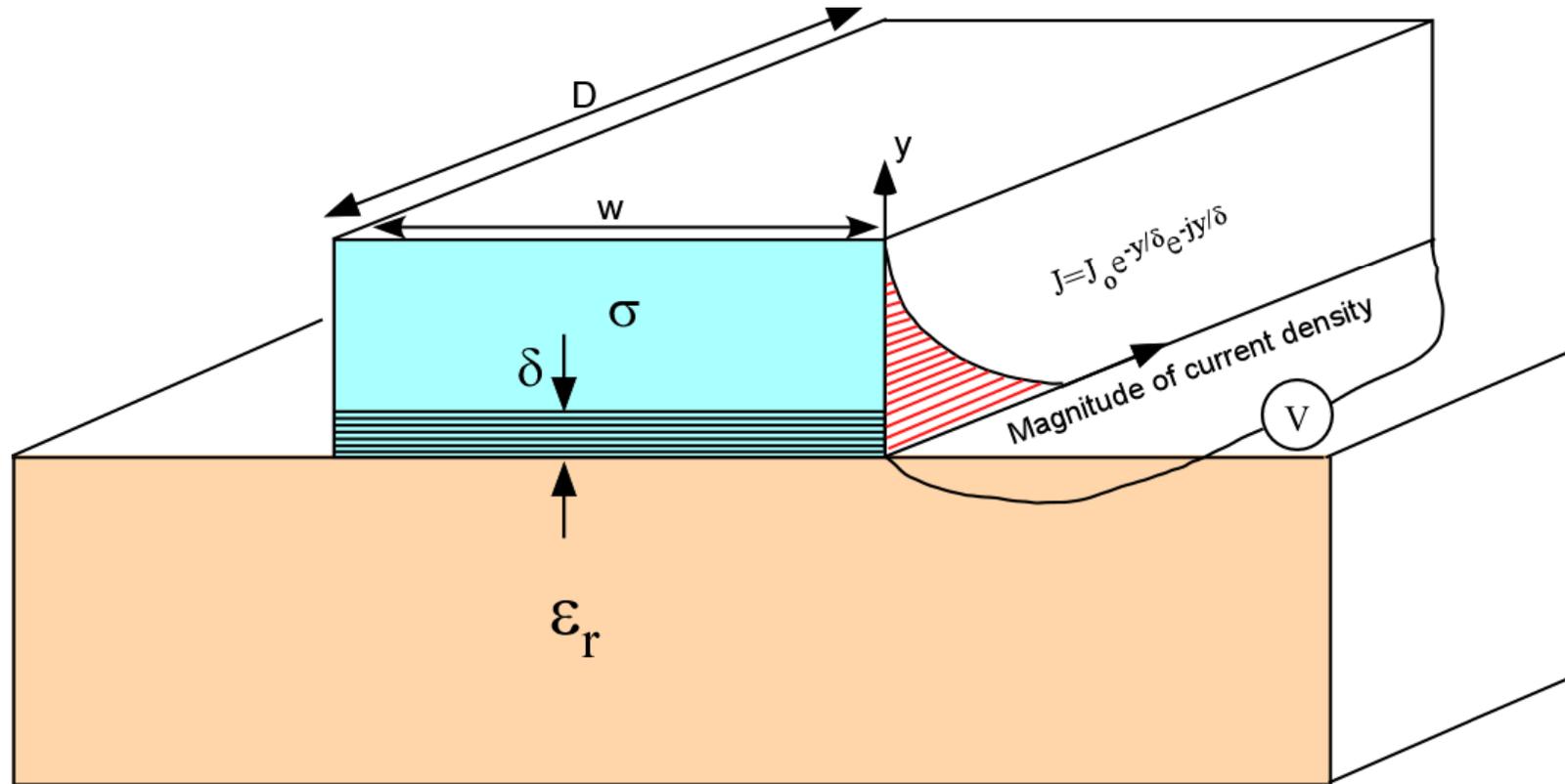
Frequency-Dependent Resistance

FREQUENCY-DEPENDENT RESISTANCE

Resistance changes with $\sqrt{f}$

$$R_{ac} = \frac{1}{w}\sqrt{\frac{\pi f \mu}{\sigma}}$$

$$R_{dc} = \frac{1}{\sigma w t}$$

Resistance is ~ constant when $\delta > t$

y-axis: AC Resistance (Ohms)
x-axis: Frequency (MHz)

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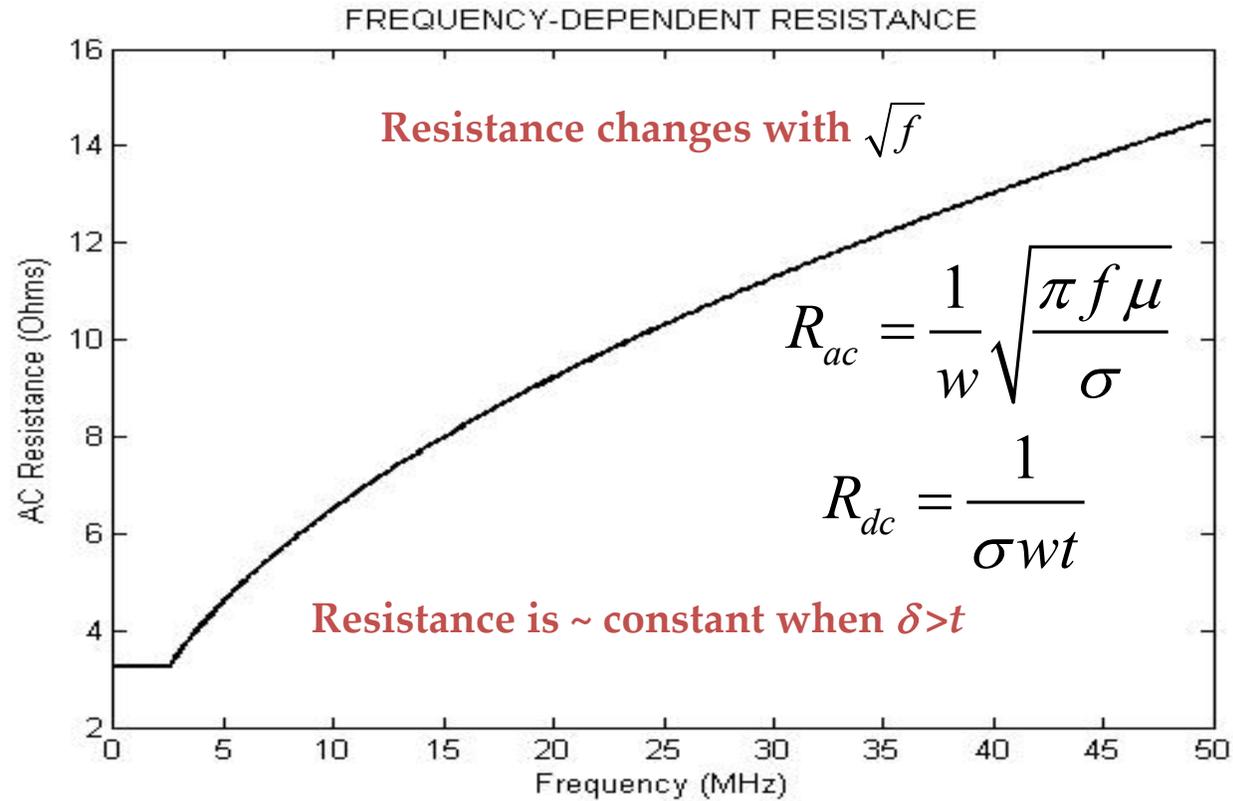
Reference Plane Current

$$R_{ac,ground} \approx \frac{l}{6h}\sqrt{\frac{\pi \mu f}{\sigma}}$$

Skin Effect in Microstrip

H. A. Wheeler, "Formulas for the skin effect," Proc. IRE, vol. 30, pp. 412-424,1942

Skin Effect in Microstrip

Current density varies as

$$J = J_o e^{-y/\delta} e^{-jy/\delta}$$

Note that the phase of the current density varies as a function of y

$$I = \int_0^\infty J_o w e^{-y/\delta} e^{-jy/\delta} dy = \frac{J_o w \delta}{1+j}$$

$$\sigma E_o = J_o \Rightarrow E_o = \frac{J_o}{\sigma}$$

The voltage measured over a section of conductor of length D is:

$$V = E_o D = \frac{J_o D}{\sigma}$$

Skin Effect in Microstrip

The skin effect impedance is

$$Z_{skin} = \frac{V}{I} = \frac{J_o D}{\sigma} \frac{(1+j)}{J_o w \delta} = \frac{D}{w}(1+j)\sqrt{\pi f \mu \rho}$$

where $\rho = \dfrac{1}{\sigma}$ is the bulk resistivity of the conductor

$$Z_{skin} = R_{skin} + jX_{skin}$$

with

$$R_{skin} = X_{skin} = \frac{D}{w}\sqrt{\pi f \mu \sigma}$$

➔ **Skin effect has reactive (inductive) component**

Internal Inductance

The internal inductance can be calculated directly from the ac resistance

$$L_{\text{internal}} = \frac{R_{ac}}{\omega} = \frac{R_{skin}}{\omega}$$

➔ **Skin effect resistance goes up with frequency**

➔ **Skin effect inductance goes down with frequency**

Surface Roughness

Copper surfaces are rough to facilitate adhesion to dielectric during PCB manufacturing
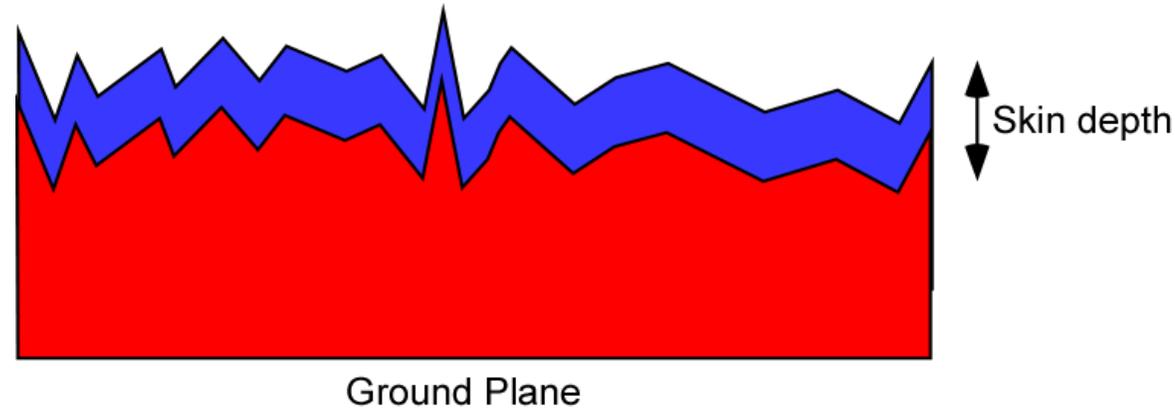
When the *tooth* height is comparable to the skin depth, roughness effects cannot be ignored

Surface roughness will increase ohmic losses

Hammerstad Model
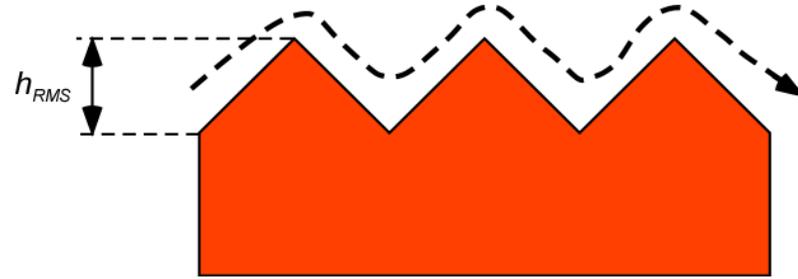
$$R_H(f) = \begin{cases} K_H R_s \sqrt{f} & \text{when } \delta < t \\ R_{dc} & \text{when } \delta \geq t \end{cases}$$

$$L_H(f) = \begin{cases} L_{external} + \dfrac{R_H(f)}{2\pi f} & \text{when } \delta < t \\ L_{external} + \dfrac{R_H(f_{\delta=t})}{2\pi f_{\delta=t}} & \text{when } \delta \geq t \end{cases}$$
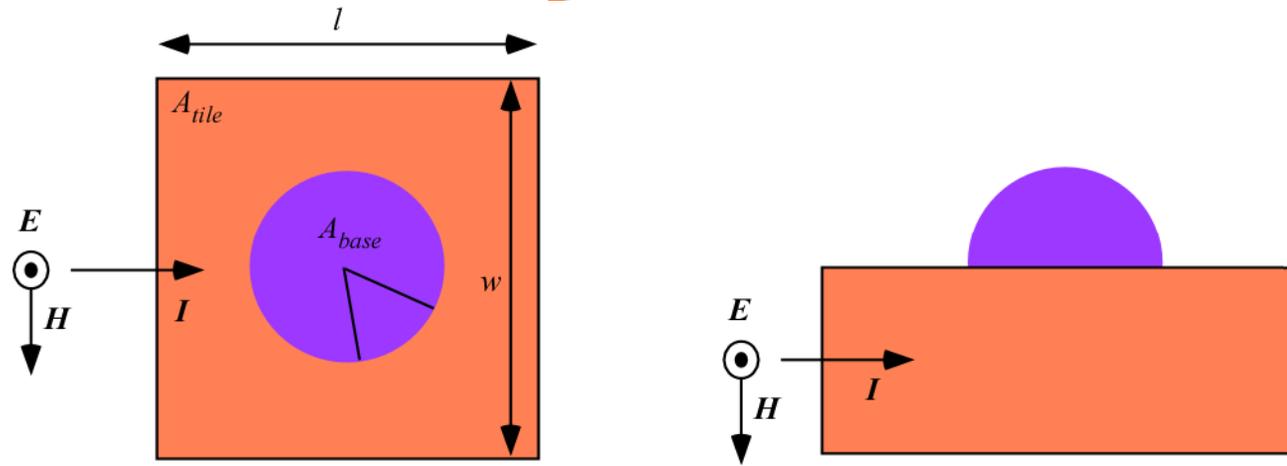
Hammerstad Model
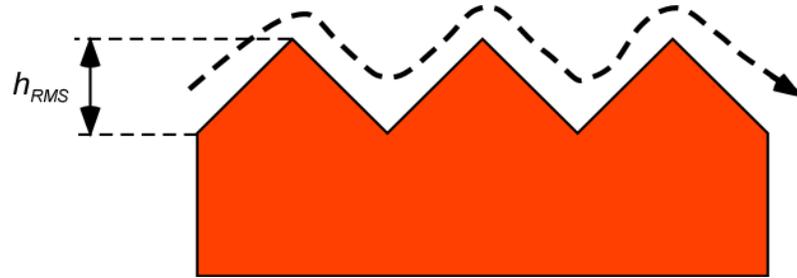
$$K_H = 1 + \frac{2}{\pi} \arctan\left[1.4 \left(\frac{h_{RMS}}{\delta} \right)^2 \right]$$

h_{RMS}: root mean square value of surface roughness height

δ: skin depth

$f_{\delta=t}$: frequency where the skin depth is equal to the thickness of the conductor

Hemispherical Model

$$R_{hemi}(f) = \begin{cases} K_{hemi} R_s \sqrt{f} & \text{when } \delta < t \\ R_{dc} & \text{when } \delta \geq t \end{cases}$$

$$L_{hemi}(f) = \begin{cases} L_{external} + \dfrac{R_{hemi}(f)}{2\pi f} & \text{when } \delta < t \\ L_{external} + \dfrac{R_{hemi}(f_{\delta=t})}{2\pi f_{\delta=t}} & \text{when } \delta \geq t \end{cases}$$
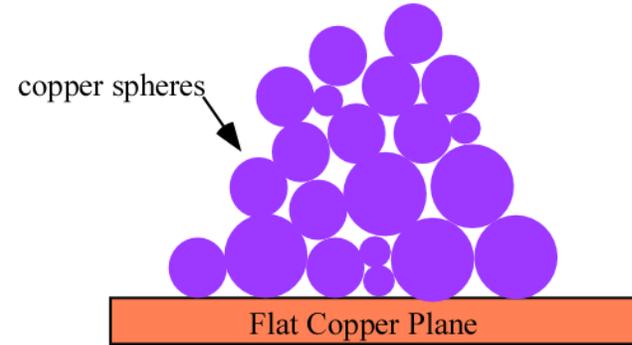
Hemispherical Model

$$K_{hemi} = \begin{cases} 1 & \text{when} \quad K_s \leq 1 \\ K_s & \text{when} \quad K_s > 1 \end{cases}$$

$$K_s = \frac{\left| \text{Re}\left[\eta \left(3\pi / 4k^2 \right) \left(\alpha(1) + \beta(1) \right) \right] \right| + \left(\mu_o \omega \delta / 4 \right) \left(A_{tile} - A_{base} \right)}{\left(\mu_o \omega \delta / 4 \right) A_{tile}}$$

$$\alpha(1) = -\frac{2j}{3}(kr)^3 \frac{1 - (\delta / r)(1 + j)}{1 + (\delta / 2r)(1 + j)}$$

$$\beta(1) = -\frac{2j}{3}(kr)^3 \frac{1 - (4j / k^2 r \delta)(1 / (1 - j))}{1 + (2j / k^2 r \delta)(1 / (1 - j))}$$

Huray Model

copper spheres

Flat Copper Plane

$$R_{Huray}(f) = \begin{cases} K_{Huray} R_s \sqrt{f} & \text{when } \delta < t \\ R_{dc} & \text{when } \delta \geq t \end{cases}$$

$$L_{Huray}(f) = \begin{cases} L_{external} + \dfrac{R_{Huray}(f)}{2\pi f} & \text{when } \delta < t \\ \\ L_{external} + \dfrac{R_{Huray}(f_{\delta=t})}{2\pi f_{\delta=t}} & \text{when } \delta \geq t \end{cases}$$

Huray Model

$$K_{Huray} = \frac{P_{flat} + P_{N\_spheres}}{P_{flat}}$$

$$P_{N\_spheres} = -\sum_{n=1}^{N} \text{Re}\left[\frac{1}{2}\eta |H_o|^2 \frac{3\pi}{k^2}\alpha(1) + \beta(1)\right]_n$$

$$P_{flat} = \left(\mu_o \omega \delta / 4\right) A_{tile} \qquad \eta = \sqrt{\mu_o / \varepsilon_o \varepsilon'}$$

H_o: magnitude of applied H field.

$$\alpha(1) = -\frac{2j}{3}(kr)^3 \frac{1-(\delta/r)(1+j)}{1+(\delta/2r)(1+j)}$$

$$\beta(1) = -\frac{2j}{3}(kr)^3 \frac{1-\left(4j/k^2 r\delta\right)\left(1/(1-j)\right)}{1+\left(2j/k^2 r\delta\right)\left(1/(1-j)\right)}$$

Dielectrics and Polarization

No field

Applied field
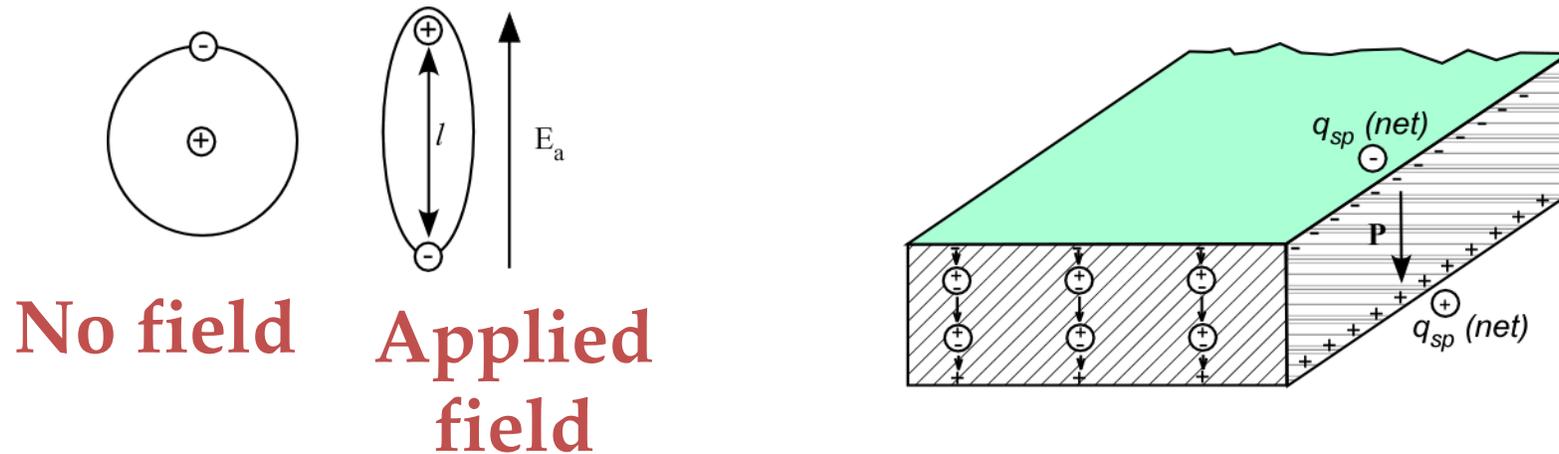
Field causes the formation of dipoles ➡ polarization

Bound surface charge density $-q_{sp}$ on upper surface and $+q_{sp}$ on lower surface of the slab.

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Dielectrics and Polarization

$$\vec{D} = \varepsilon_o \vec{E}_a + \vec{P} = \varepsilon_o \vec{E}_a + \varepsilon_o \chi_e \vec{E}_a = \varepsilon_o \left(1 + \chi_e\right) \vec{E}_a = \varepsilon_s \vec{E}_a$$

$\vec{P}$: polarization vector

$\vec{D}$: electric flux density

$\vec{E}_a$: applied electric field

χ_e : electric susceptibility

ε_o : free-space permittivity

ε_s : static permittivity
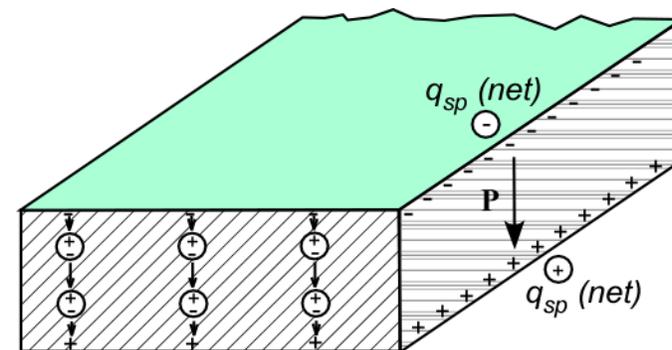
Dielectric Constant

Material	ε_r
Air	1.0006
Styrofoam	1.03
Paraffin	2.1
Teflon	2.1
Plywood	2.1
RT/duroid 5880	2.20
Polyethylene	2.26
RT/duroid 5870	2.35
Glass-reinforced teflon (microfiber)	2.32-2.40
Teflon quartz (woven)	2.47
Glass-reinforced teflon (woven)	2.4-2.62
Cross-linked polystyrene (unreinforced)	2.56
Polyphenelene oxide (PPO)	2.55
Glass-reinforced polystyrene	2.62
Amber	3
Rubber	3
Plexiglas	3.4

Dielectric Constants

Material	ε_r
Lucite	3.6
Fused silica	3.78
Nylon (solid)	3.8
Quartz	3.8
Bakelite	4.8
Formica	5
Lead glass	6
Mica	6
Beryllium oxide (BeO)	6.8-7.0
Marble	8
Flint glass	10
Ferrite (FqO,)	12-16
Silicon (Si)	12
Gallium arsenide (GaAs)	13
Ammonia (liquid)	22
Glycerin	50
Water	81

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AC Variations

When a material is subjected to an applied electric field, the centroids of the positive and negative charges are displaced relative to each other forming a linear dipole.

When the applied fields begin to alternate in polarity, the permittivities are affected and become functions of the frequency of the alternating fields.

AC Variations

Reverses in polarity cause incremental changes in the static conductivity σ_s➜heating of materials using microwaves (e.g. food cooking)

When an electric field is applied, it is assumed that the positive charge remains stationary and the negative charge moves relative to the positive along a platform that exhibits a friction (damping) coefficient d.

Complex Permittivity

$$\varepsilon_r' = 1 + \frac{\dfrac{N_e Q^2}{\varepsilon_o m}\left(\omega_o^2 - \omega^2\right)}{\left(\omega_o^2 - \omega^2\right)^2 + \left(\omega\dfrac{d}{m}\right)^2}$$

$$\varepsilon_r'' = \frac{N_e Q^2}{\varepsilon_o m}\left[\frac{\omega\dfrac{d}{m}}{\left(\omega_o^2 - \omega^2\right)^2 + \left(\omega\dfrac{d}{m}\right)^2}\right]$$

$$\omega_o = \sqrt{\frac{s}{m}}$$

N_e : **dipole density**

Q : **dipole charge**

ε_o : **free space permittivity**

s : **spring (tension) factor**

m : **mass**

d : **damping coefficient**

ω_o : **natural frequency**

ω : **applied frequency**

Complex Permittivity

$$\nabla \times \vec{H} = \vec{J}_i + \vec{J}_c + j\omega\dot{\varepsilon}\vec{E} = \vec{J}_i + \sigma_s\vec{E} + j\omega\left(\varepsilon' - j\varepsilon''\right)\vec{E}$$

$$\nabla \times \vec{H} = \vec{J}_i + \left(\sigma_s + \omega\varepsilon''\right)\vec{E} + j\omega\varepsilon'\vec{E} = \vec{J}_i + \sigma_e\vec{E} + j\omega\varepsilon'\vec{E}$$

$$\sigma_e = \text{equivalent conductivity} = \sigma_s + \omega\varepsilon'' = \sigma_s + \sigma_a$$

$$\sigma_a = \text{alternating field conductivity} = \omega\varepsilon''$$

$$\sigma_s = \text{static field conductivity}$$

σ_e: total conductivity composed of the static portion σ_s and the alternative part σ_a caused by the rotation of the dipoles

Complex Permittivity

$$\vec{J}_t = \vec{J}_i + \vec{J}_{ce} + \vec{J}_{de} = \vec{J}_i + \sigma_e \vec{E} + j\omega\varepsilon' \vec{E}$$

$\vec{J}_t$: total electric current density

$\vec{J}_i$: impressed (source) electric current density

$\vec{J}_{ce}$: effective electric conduction current density

$\vec{J}_{de}$: effective displacement electric current density

$$\vec{J}_t = \vec{J}_i + \sigma_e \vec{E} + j\omega\varepsilon' \vec{E} = \vec{J}_i + j\omega\varepsilon' \left(1 - j\frac{\sigma_e}{\omega\varepsilon'}\right)\vec{E} = \vec{J}_i + j\omega\varepsilon'\left(1 - j\tan\delta_e\right)\vec{E}$$

$$\tan\delta_e = \text{effective electric loss tangent} = \frac{\sigma_e}{\omega\varepsilon'} = \frac{\sigma_s + \sigma_a}{\omega\varepsilon'} = \frac{\sigma_s}{\omega\varepsilon'} + \frac{\sigma_a}{\omega\varepsilon'}$$

Complex Permittivity

$$\tan \delta_e = \frac{\sigma_s}{\omega \varepsilon'} + \frac{\varepsilon''}{\varepsilon'} = \tan \delta_s + \tan \delta_a = \frac{\varepsilon_e''}{\varepsilon_e'}$$

$$\tan \delta_s = \text{static electric loss tangent} = \frac{\sigma_s}{\omega \varepsilon'}$$

$$\tan \delta_a = \text{alternating electric loss tangent} = \frac{\sigma_a}{\omega \varepsilon'} = \frac{\varepsilon''}{\varepsilon'}$$

$$\vec{J}_{cd} = \vec{J}_{ce} + \vec{J}_{de} = \sigma_e \vec{E} + j\omega\varepsilon' \vec{E} = j\omega\varepsilon' \left(1 - j\frac{\sigma_e}{\omega\varepsilon'} \right) \vec{E} = j\omega\varepsilon' \left(1 - j\tan\delta_e \right) \vec{E}$$

$J_{cd} = J_{ce} + J_{de}$ $J_{de} = j\omega\varepsilon'E$

$J_{ce} = \sigma_e E$
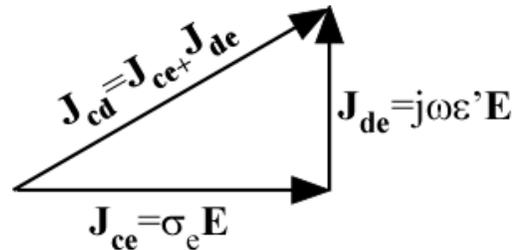
Dielectric Properties

Good Dielectrics: $\qquad \dfrac{\sigma_e}{\omega \varepsilon'} \ll 1$

$$\vec{J}_{cd} = j\omega\varepsilon'\left(1 - j\frac{\sigma_e}{\omega\varepsilon'}\right)\vec{E} \simeq j\omega\varepsilon'\vec{E}$$

Good Conductors: $\qquad \dfrac{\sigma_e}{\omega \varepsilon'} \gg 1$

$$\vec{J}_{cd} = j\omega\varepsilon'\left(1 - j\frac{\sigma_e}{\omega\varepsilon'}\right)\vec{E} \simeq \sigma_e\vec{E}$$

Dielectric Properties

Good Dielectrics: $\quad \dfrac{\sigma_e}{\omega \varepsilon'} \ll 1$

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Good Conductors: $\quad \dfrac{\sigma_e}{\omega \varepsilon'} \gg 1$

$$\vec{J}_{cd} = j\omega\varepsilon'\left(1 - j\frac{\sigma_e}{\omega\varepsilon'}\right)\vec{E} \simeq \sigma_e\vec{E}$$

Kramers-Kronig Relations

There is a relation between the real and imaginary parts of the complex permittivity:

$$\varepsilon_r^{'}(\omega) = 1 + \frac{2}{\pi}\int_0^\infty \frac{\omega'\varepsilon_r^{''}(\omega')}{(\omega')^2 - \omega^2}d\omega'$$

$$\varepsilon_r^{''}(\omega) = \frac{2\omega}{\pi}\int_0^\infty \frac{1-\varepsilon_r^{'}(\omega')}{(\omega')^2 - \omega^2}d\omega'$$

Debye Equation

$$\dot{\varepsilon}_r(\omega) = \varepsilon_r^{'}(\omega) - j\varepsilon_r^{''}(\omega) = \varepsilon_{r\infty}^{'} + \frac{\varepsilon_{rs}^{'} - \varepsilon_{r\infty}^{'}}{1+j\omega\tau_e}$$

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Kramers-Kronig Relations

τ_e is a relaxation time constant:

$$\tau_e = \tau \frac{\varepsilon'_{rs} + 2}{\varepsilon'_{r\infty} + 2}$$

$$\varepsilon'_r(\omega) = \varepsilon'_{r\infty} + \frac{\varepsilon'_{rs} - \varepsilon'_{r\infty}}{1 + (\omega\tau_e)^2} \qquad \varepsilon''_r(\omega) = \frac{(\varepsilon'_{rs} - \varepsilon'_{r\infty})\omega\tau_e}{1 + (\omega\tau_e)^2}$$

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Dielectric Materials

Material	ε_r'	$\tan\delta$
Air	1.0006	
Alcohol (ethyl)	25	0.1
Aluminum oxide	8.8	6×10^{-4}
Bakelite	4.74	22×10^{-3}
Carbon dioxide	1.001	
Germanium	16	
Glass	4*7	1×10^{-3}
Ice	4.2	0.1
Mica	5.4	6×10^{-4}
Nylon	3.5	2×10^{-2}
Paper	3	8×10^{-3}
Plexiglas	3.45	4×10^{-2}
Polystyrene	2.56	5×10^{-5}
Porcelain	6	14×10^{-3}

Dielectric Materials

Material	ε_r'	$\tan\delta$
Pyrex glass	4	6×10^{-4}
Quartz (fused)	3.8	7.5×10^{-4}
Rubber	2.5-3	2×10^{-3}
Silica (fused)	3.8	7.5×10^{-4}
Silicon	11.8	
Snow	3.3	0.5
Sodium chloride	5.9	1×10^{-4}
Soil (dry)	2.8	7×10^{-2}
Styrofoam	1.03	1×10^{-4}
Teflon	2.1	3×10^{-4}
Titanium dioxide	100	15×10^{-4}
Water (distilled)	80	4×10^{-2}
Water (sea)	81	4.64
Water (dehydrated)	1	0
Wood (dry)	1.5-4	1×10^{-2}

PCB Stackup

Source: H. Barnes et al, "ATE Interconnect Performance to 43 Gps Using Advanced PCB Materials", DesignCon 2008

Differential Signaling

Differential signaling is widely used in the industry today. High-speed serial interfaces such as PCI-E, XAUI, OC768, and CEI use differential signaling for transmitting and receiving data in point-to-point topology between a driver (TX) and receiver (RX) connected by a differential pair.
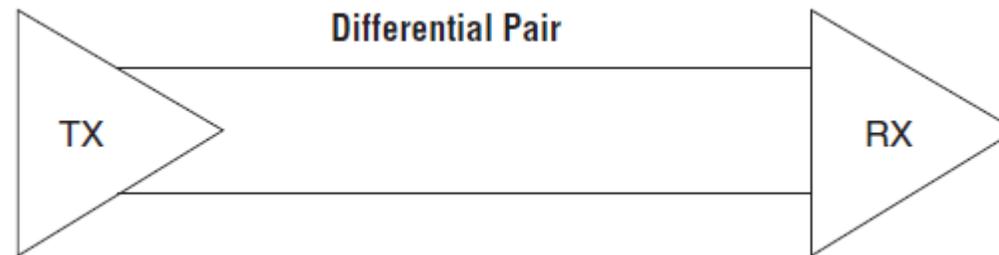
The skew (time delay) between the two traces of the differential pair should be zero. Any skew between the two traces causes the differential signal to convert into a common signal.

Fiber Weave Effect

Fiberglass weave pattern causes signals to propagate at different speeds in differential pairs
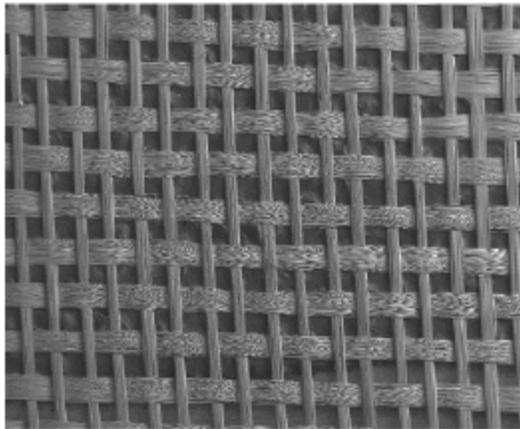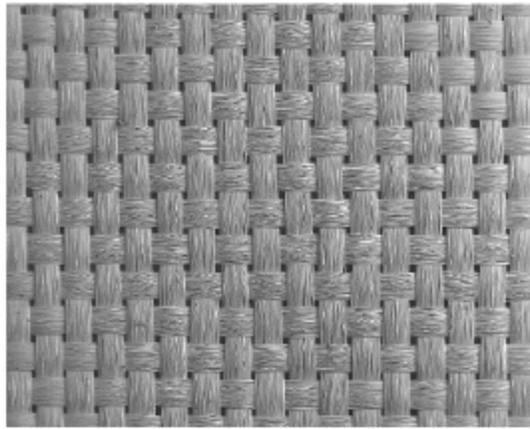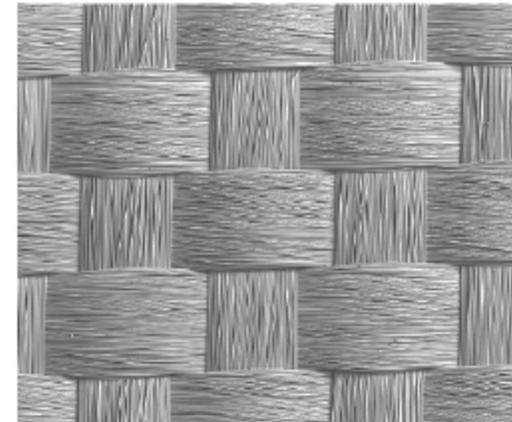
1080   2116   7628

Source: S. McMorrow, C. Heard, "The Impact of PCB Laminate Weave on the Electrical Performance of Differential Signaling at Multi-Gigabit Data Rates", DesignCon 2005.
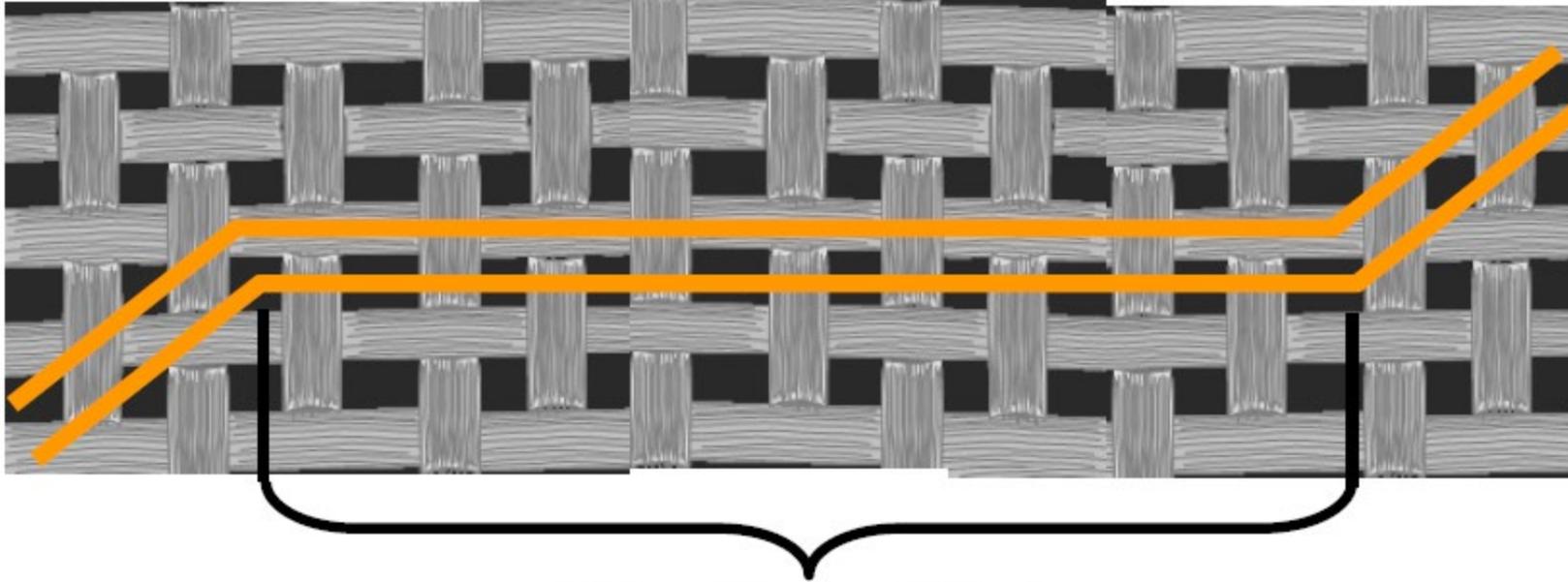
Fiber Weave Effect

Fiber Weave Effect

Source: Lambert Simonovich, "Practical Fiber Weave Effect Modeling",
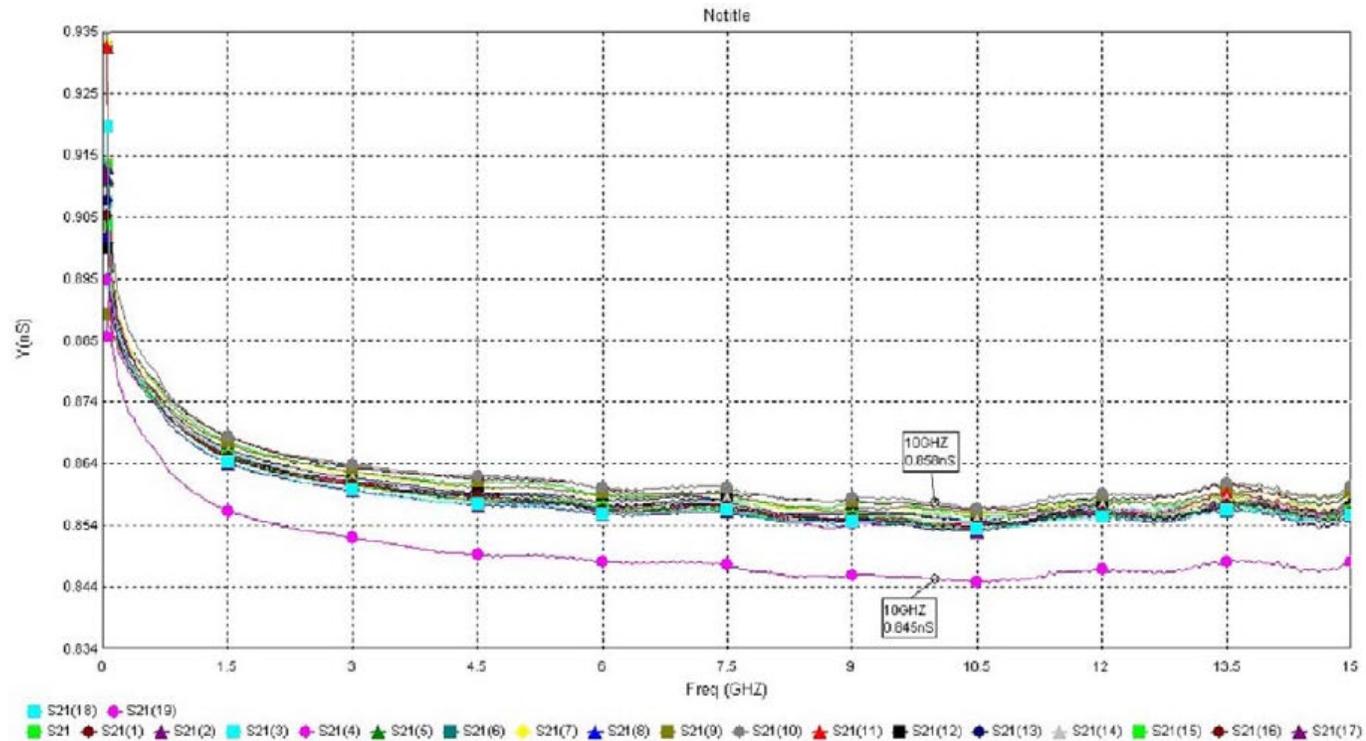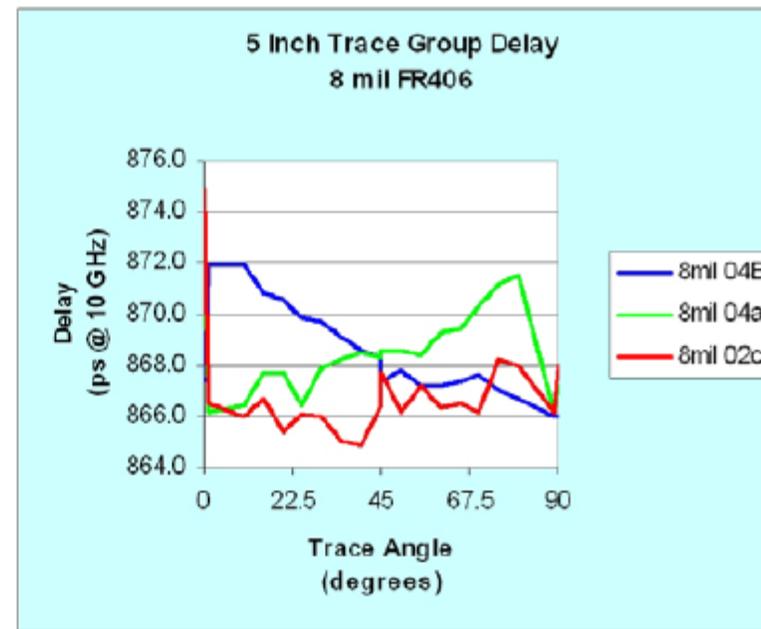White Paper-Issue 3, March 2, 2012.

Fiber Weave Effect
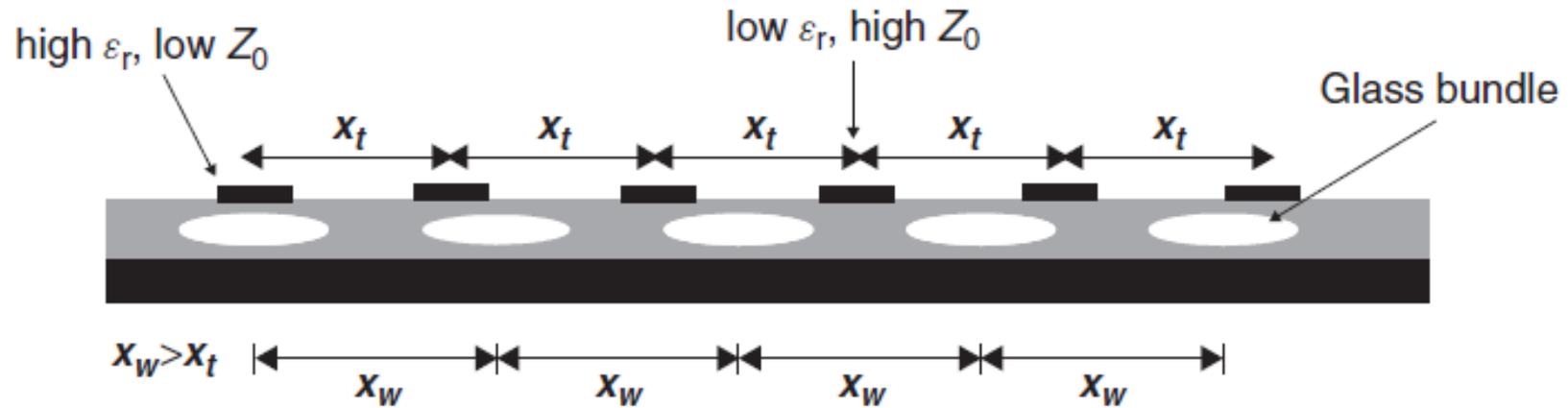
Source: S. Hall and H. Heck , Advanced Signal Integrity for High-Speed Digital Designs, J. Wiley, IEEE , 2009.
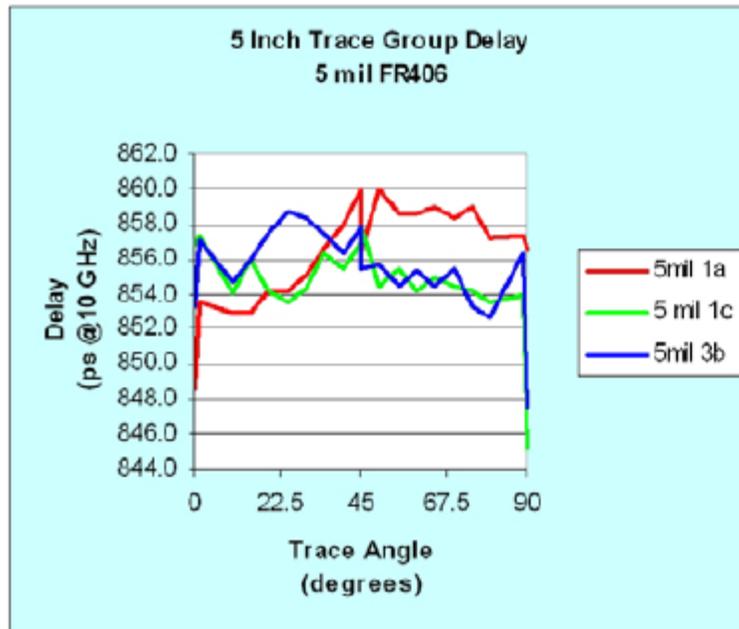
Fiber Weave Effect

Group delay variation

Source: S. McMorrow, C. Heard, "The Impact of PCB Laminate Weave on the Electrical Performance of Differential Signaling at Multi-Gigabit Data Rates", DesignCon 2005.
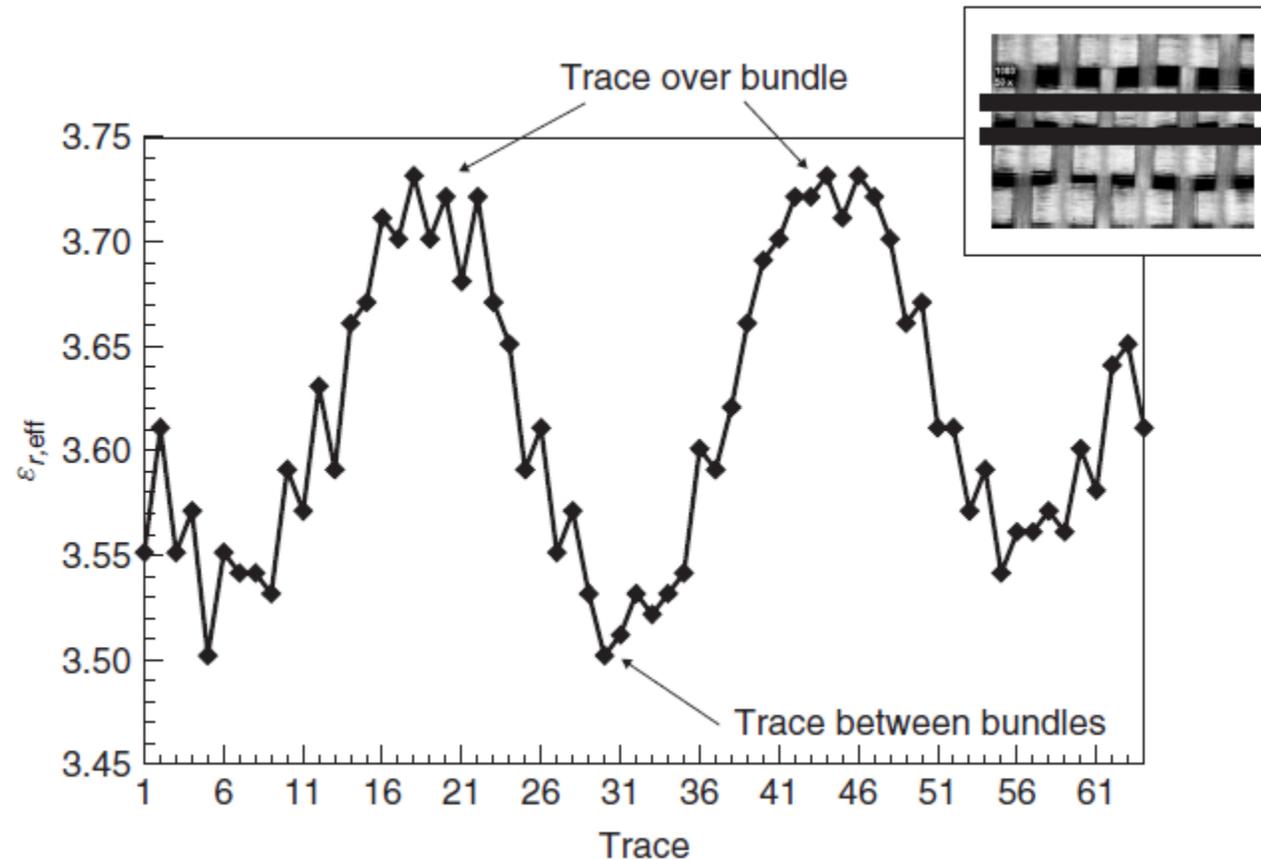
Fiber Weave Effect

Group delay variation: effect of angle

Source: S. McMorrow, C. Heard, "The Impact of PCB Laminate Weave on the Electrical Performance of Differential Signaling at Multi-Gigabit Data Rates", DesignCon 2005.
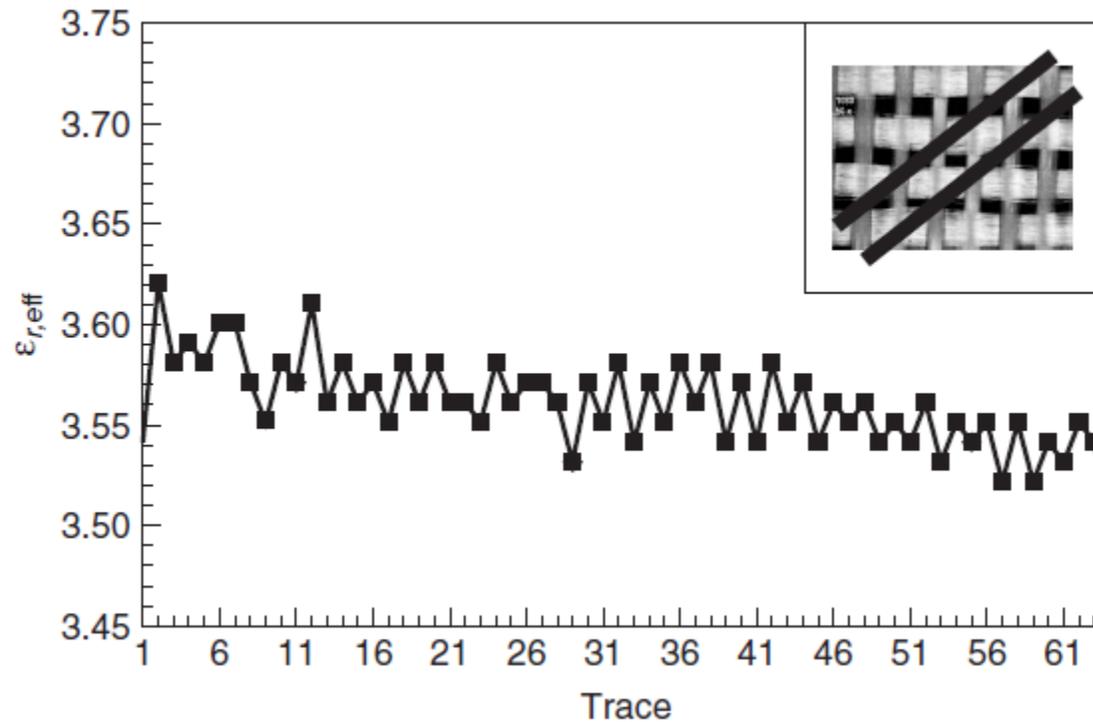
Fiber Weave Effect

Straight traces

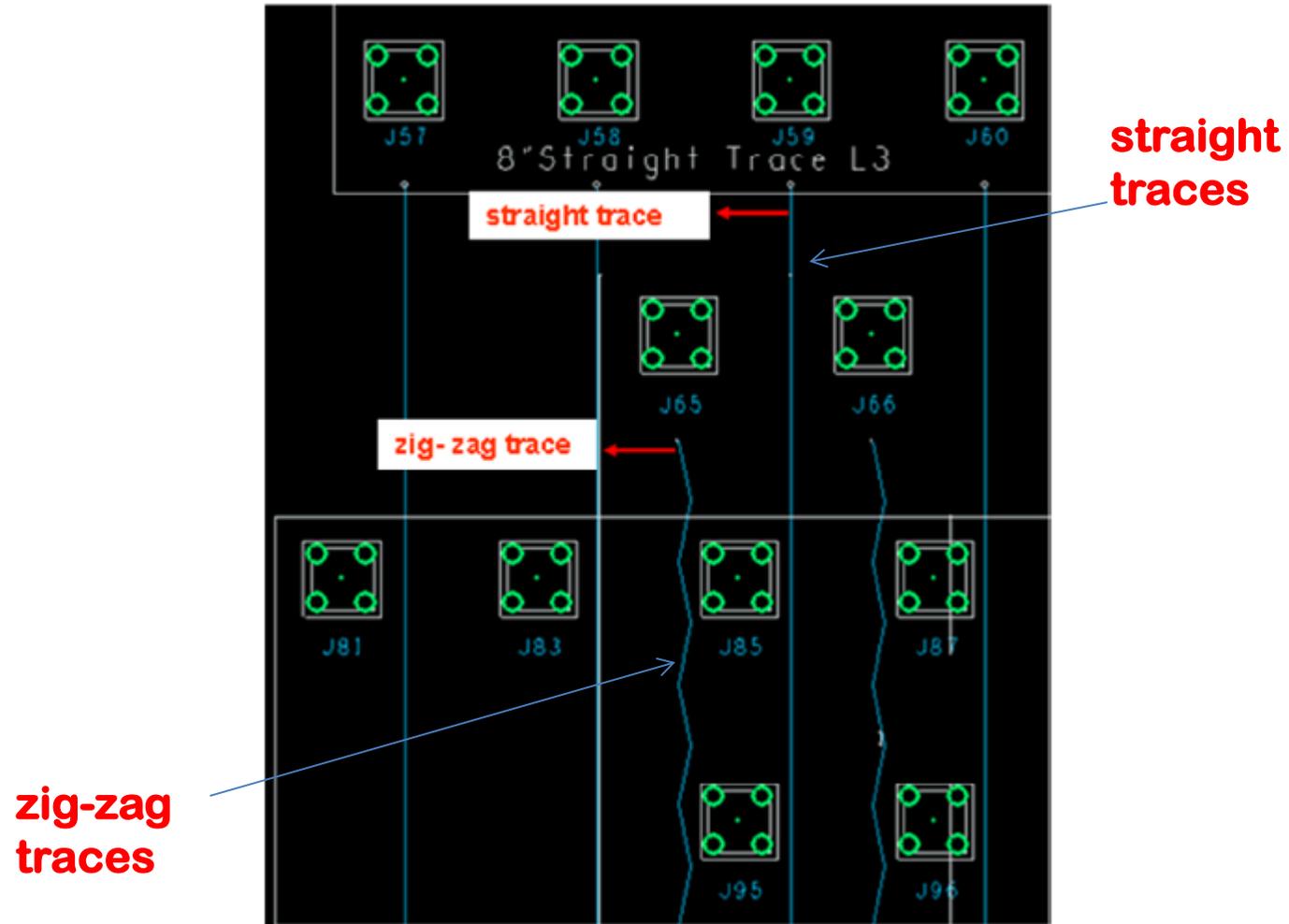Source: S. Hall and H. Heck , Advanced Signal Integrity for High-Speed Digital Designs, J. Wiley, IEEE , 2009.

Fiber Weave Effect

45° traces

Source: S. Hall and H. Heck , Advanced Signal Integrity for High-Speed Digital Designs, J. Wiley, IEEE , 2009.
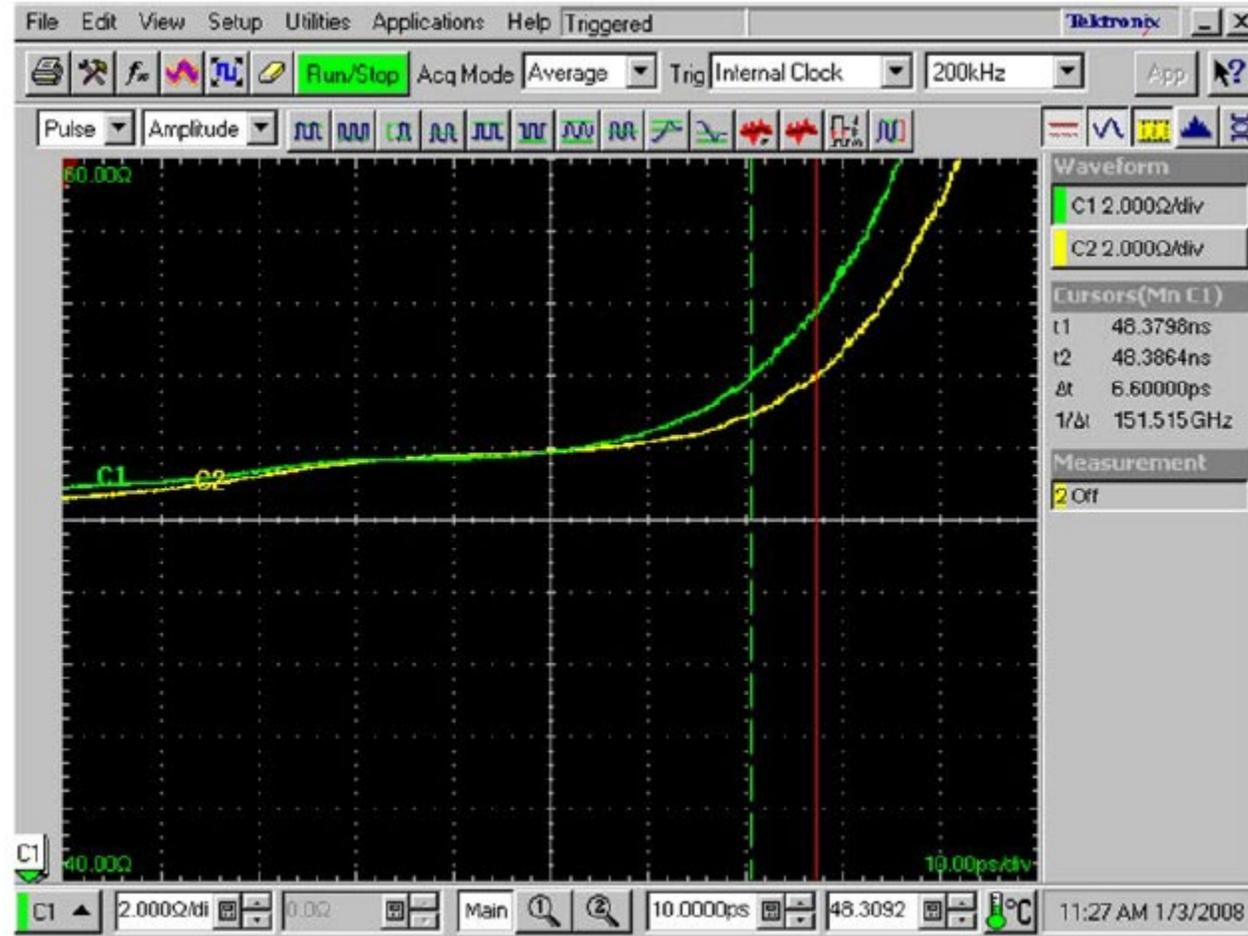
Fiber Weave Effect

Source: PCB Dielectric Material Selection and Fiber Weave Effect on High-Speed Channel Routing, Altera Application Note AN-528-1.1, January 2011.

Fiber Weave Effect

Skew on straight traces

Source: PCB Dielectric Material Selection and Fiber Weave Effect on High-Speed Channel Routing, Altera Application Note AN-528-1.1, January 2011.

Fiber Weave Effect

Skew on zig-zag traces

Source: PCB Dielectric Material Selection and Fiber Weave Effect on High-Speed Channel Routing, Altera Application Note AN-528-1.1, January 2011.

Fiber Weave Effect

- **Mitigation Techniques**
  - ➤ Use wider widths to achieve impedance targets.
  - ➤ Specify a denser weave (2116, 2113, 7268, 1652) compared to a sparse weave (106, 1080).
  - ➤ Move to a better substrate such as Nelco 4000-13
  - ➤ Perform floor planning such that routing is at an angle rather than orthogonal.
  - ➤ Make use of zig-zag routing